

Marc Portail

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

57
papers

356
citations

10
h-index

16
g-index

58
ext. papers

406
ext. citations

1.5
avg, IF

3.27
L-index

#	Paper	IF	Citations
57	Oxygen isotope variations in Mg-rich olivines from type I chondrules in carbonaceous chondrites. <i>Geochimica Et Cosmochimica Acta</i> , 2022 , 319, 73-93	5.5	0
56	Metalorganic Chemical Vapor Phase Epitaxy Growth of Buffer Layers on 3C-SiC/Si(111) Templates for AlGaN/GaN High Electron Mobility Transistors with Low RF Losses. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900760	1.6	1
55	Pendeo-epitaxy of GaN on SOI nano-pillars: Freestanding and relaxed GaN platelets on silicon with a reduced dislocation density. <i>Journal of Crystal Growth</i> , 2019 , 526, 125235	1.6	1
54	Buried defects induced by plasma assisted molecular beam epitaxy of AlN and GaN on Silicon. <i>Journal of Crystal Growth</i> , 2019 , 507, 220-225	1.6	1
53	Chondrules as direct thermochemical sensors of solar protoplanetary disk gas. <i>Science Advances</i> , 2018 , 4, eaar3321	14.3	37
52	A comparative study of graphene growth on SiC by hydrogen-CVD or Si sublimation through thermodynamic simulations. <i>CrystEngComm</i> , 2018 , 20, 3702-3710	3.3	4
51	Screening and engineering of colour centres in diamond. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 483002	3	44
50	Structural Quality, Polishing and Thermal Stability of 3C-SiC/Si Templates. <i>Materials Science Forum</i> , 2018 , 924, 306-309	0.4	9
49	Influence of Aluminum Incorporation on Mechanical Properties of 3C-SiC Epilayers. <i>Materials Science Forum</i> , 2018 , 924, 318-321	0.4	2
48	Turning the undesired voids in silicon into a tool: In-situ fabrication of free-standing 3C-SiC membranes. <i>Applied Physics Letters</i> , 2017 , 110, 081602	3.4	3
47	Ion-induced interdiffusion of surface GaN quantum dots. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017 , 409, 107-110	1.2	
46	Influence of Growth Temperature on Site Competition Effects during Chemical Vapor Deposition of 4H-SiC Layers. <i>Materials Science Forum</i> , 2017 , 897, 79-82	0.4	
45	CVD Growth of Graphene on SiC (0001): Influence of Substrate Offcut. <i>Materials Science Forum</i> , 2017 , 897, 731-734	0.4	3
44	A detailed study of AlN and GaN grown on silicon-on-porous silicon substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600450	1.6	2
43	Structural Study of the Innovative 3C-SiC/Si/3C-SiC/Si Heterostructure for Electro-Mechanical Applications. <i>Materials Science Forum</i> , 2016 , 858, 143-146	0.4	2
42	Novel 3C-SiC Microstructure for MEMS Applications. <i>Materials Science Forum</i> , 2016 , 858, 723-728	0.4	1
41	GaN films and GaN/AlGaIn quantum wells grown by plasma assisted molecular beam epitaxy using a high density radical source. <i>Journal of Crystal Growth</i> , 2016 , 433, 165-171	1.6	6

40	Realization of minimum number of rotational domains in heteroepitaxied Si(110) on 3C-SiC(001). <i>Applied Physics Letters</i> , 2016 , 108, 011608	3.4	4
39	On the interplay between Si(110) epilayer atomic roughness and subsequent 3C-SiC growth direction. <i>Journal of Applied Physics</i> , 2016 , 120, 185306	2.5	3
38	p-Type Doping of 4H- and 3C-SiC Epitaxial Layers with Aluminum. <i>Materials Science Forum</i> , 2016 , 858, 137-142	0.4	13
37	Toward high-quality 3CβSiC membrane on a 3CβSiC pseudo-substrate. <i>Materials Letters</i> , 2015 , 160, 28-30	3.3	5
36	Structural Investigation of Si Quantum Dots Grown by CVD on AlN/Si(111) and 3C-SiC/Si(100) Epilayers. <i>Materials Science Forum</i> , 2015 , 821-823, 1003-1006	0.4	
35	Influence of Site Competition Effects on Dopant Incorporation during Chemical Vapor Deposition of 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2015 , 821-823, 149-152	0.4	1
34	Direct insight into grains formation in Si layers grown on 3C-SiC by chemical vapor deposition. <i>Acta Materialia</i> , 2015 , 98, 336-342	8.4	12
33	Silicon Growth on 3C-SiC(001)/Si(001): Pressure Influence and Thermal Effect. <i>Materials Science Forum</i> , 2015 , 821-823, 978-981	0.4	5
32	Rotated domain network in graphene on cubic-SiC(001). <i>Nanotechnology</i> , 2014 , 25, 135605	3.4	12
31	Influence of 3CβSiC/Si (111) template properties on the strain relaxation in thick GaN films. <i>Journal of Crystal Growth</i> , 2014 , 398, 23-32	1.6	12
30	Investigation of structural and electronic properties of epitaxial graphene on 3C-SiC(100)/Si(100) substrates. <i>Nanotechnology, Science and Applications</i> , 2014 , 7, 85-95	3.9	7
29	Investigation of Aluminum Incorporation in 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2014 , 806, 45-50	0.4	2
28	3C-SiC: New Interest for MEMS Devices. <i>Materials Science Forum</i> , 2014 , 806, 3-9	0.4	3
27	X-Ray Diffraction and Raman Spectroscopy Study of Strain in Graphene Films Grown on 6H-SiC(0001) Using Propane-Hydrogen-Argon CVD. <i>Materials Science Forum</i> , 2013 , 740-742, 117-120	0.4	10
26	Structural and Electrical Properties of Graphene Films Grown by Propane/Hydrogen CVD on 6H-SiC(0001). <i>Materials Science Forum</i> , 2012 , 717-720, 625-628	0.4	3
25	Ti Thickness Influence for Ti/Ni Ohmic Contacts on N-Type 3C-SiC. <i>Materials Science Forum</i> , 2012 , 711, 179-183	0.4	4
24	Dose Influence on Physical and Electrical Properties of Nitrogen Implantation in 3C-SiC on Si. <i>Materials Science Forum</i> , 2012 , 711, 154-158	0.4	4
23	Detailed Experimental Study of Mean and Gradient Stresses in Thin 3C-SiC Films Performed Using Micromachined Cantilevers. <i>Materials Science Forum</i> , 2012 , 711, 84-88	0.4	1

22	Graphene/SiC Interface Control Using Propane-Hydrogen CVD on 6H-SiC(0001) and 3C-SiC(111)/Si(111). <i>Materials Science Forum</i> , 2012 , 711, 253-257	0.4	3
21	Elaboration of Monocrystalline Si Thin Film on 3C-SiC(100)/Si Epilayers by Low Pressure Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2012 , 711, 61-65	0.4	7
20	CVD Growth of Graphene on 2BC-SiC/Si Templates: Influence of Substrate Orientation and Wafer Homogeneity. <i>Materials Science Forum</i> , 2012 , 717-720, 621-624	0.4	1
19	Electrical Characterization of Nitrogen Implanted 3C-SiC by SSRM and C ₁ s XPS Measurements. <i>Materials Science Forum</i> , 2011 , 679-680, 193-196	0.4	6
18	Analytical Model of Stress Relaxation in 3C SiC Layers on Silicon. <i>Materials Science Forum</i> , 2011 , 679-680, 79-82	0.4	3
17	Epitaxial Graphene Elaborated on 3C-SiC(111)/Si Epilayers. <i>Materials Science Forum</i> , 2010 , 645-648, 585-588	0.4	4
16	Thermally Induced Surface Reorganization of 3C-SiC(111) Epilayers Grown on Silicon Substrates. <i>Materials Science Forum</i> , 2010 , 645-648, 155-158	0.4	2
15	Micromachining of thin 3C-SiC films for mechanical properties investigation. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1246, 1		11
14	Recent Advances in Surface Preparation of Silicon Carbide and other Wide Band Gap Materials. <i>Materials Science Forum</i> , 2010 , 645-648, 753-758	0.4	11
13	Role of Substrate Misorientation in Relaxation of 3C-SiC Layers on Silicon. <i>Materials Science Forum</i> , 2009 , 615-617, 169-172	0.4	8
12	Advances in Liquid Phase Conversion of (100) and (111) Oriented Si Wafers into Self-Standing 3C-SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 49-52	0.4	1
11	Strain in 3CBiC Heteroepitaxial Layers Grown on (100) and (111) Oriented Silicon Substrates. <i>Materials Science Forum</i> , 2008 , 600-603, 207-210	0.4	5
10	P Implantation Effect on Specific Contact Resistance in 3C-SiC Grown on Si. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1068, 1		2
9	Structural and Morphological Characterization of 3C-SiC Films Grown on (111), (211) and (100) Silicon Substrates. <i>Materials Science Forum</i> , 2008 , 600-603, 231-234	0.4	6
8	AlGaN/GaN high electron mobility transistors grown on 3C-SiC/Si(1 1 1). <i>Journal of Crystal Growth</i> , 2008 , 310, 4417-4423	1.6	36
7	Low Specific Contact Resistance to 3C-SiC Grown on (100) Si Substrates. <i>Materials Science Forum</i> , 2007 , 556-557, 721-724	0.4	8
6	Trends in Dopant Incorporation for 3C-SiC Films on Silicon. <i>Materials Science Forum</i> , 2007 , 556-557, 207-210	0.4	6
5	Study by HREELS of elementary reactions on graphite surface induced by Ar ⁺ and H ⁺ ion bombardment. <i>Surface Science</i> , 2000 , 454-456, 384-389	1.8	8

4	Dynamical properties of graphite and peculiar behaviour of the low-energy plasmon. <i>Surface Science</i> , 1999 , 433-435, 863-867	1.8	11
3	Vanadium Incorporation in 3C-SiC Epilayers and its Consequences for Electrical Properties of 3C-SiC Material. <i>Materials Science Forum</i> ,1062, 140-145	0.4	
2	Designing SiC Based CMUT Structures: An Original Approach and Related Material Issues. <i>Materials Science Forum</i> ,1062, 94-98	0.4	0
1	Precise Control of Al Incorporation during CVD Growth of SiC Epilayers by Using Hydrogen Chloride. <i>Materials Science Forum</i> ,1062, 84-88	0.4	